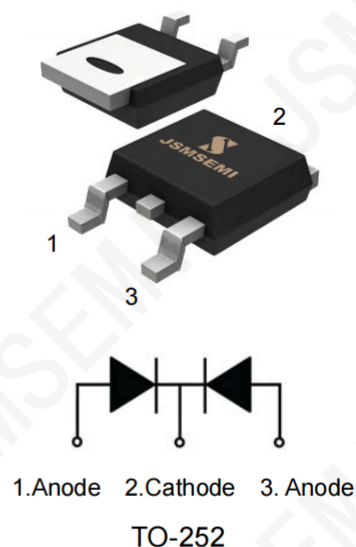


Features:

- ☐ Low power loss, high efficiency.High surge capacity
- ☐ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.
- ☐ Metal silicon junction, majority carrier conduction.
- ☐ High current Capability, low forward voltage drop.
- ☐ Guard ring for over voltage protection.



Absolute Maximum Ratings(Ta=25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Maximum Recurrent Peak Reverse Voltage		V_{RRM}	45	V
Maximum RMS Voltage		V_{RMS}	31.5	V
Maximum DC Blocking Voltage		$V_{R(DC)}$	45	V
Maximum Average Forward Current		$I_{F(AV)}$	30	A
Peak Forward Surge Current:8.3ms single half sine-wave superimposed on rated load (JEDEC method)		I_{FSM}	200	A
Maximum Forward Voltage @IF=15A Tj=25℃		V_F	0.65	V
Maximum DC Reverse Current	Tj=25℃	I_R	0.2	mA
	Tj=125℃		20	mA
Maximum Operating Junction Temperature		T_j	150	℃
Storage Temperature		T_{stg}	-40~+150	℃

Typical Characteristics

RATING AND CHARACTERISTIC CURVES

FIG. 1- FORWARD CURRENT DERATING CURVE

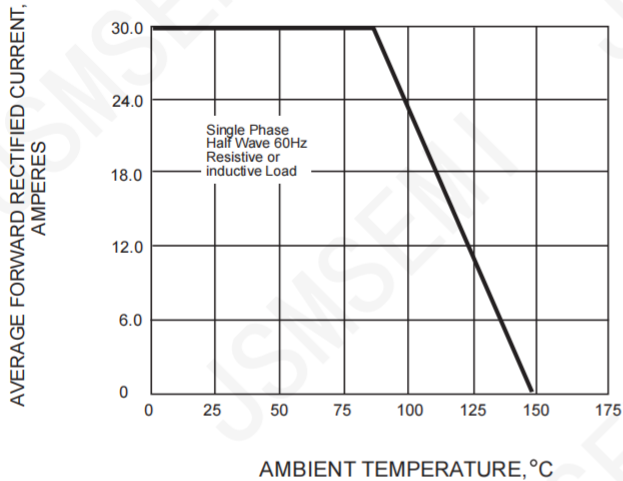


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

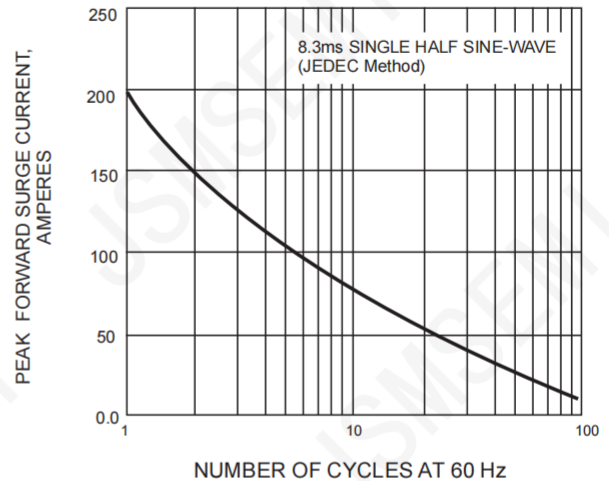


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

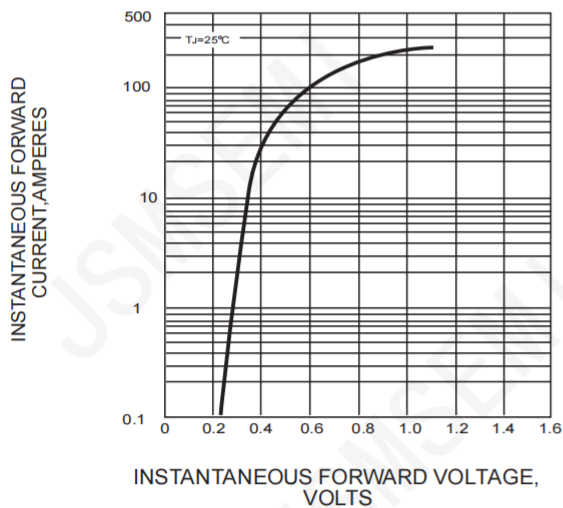
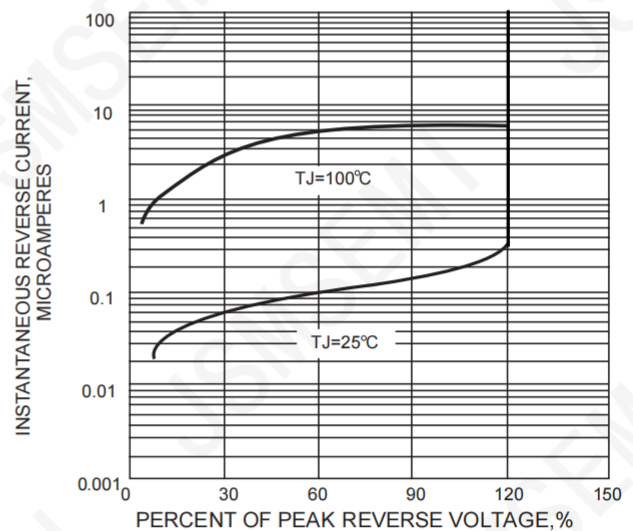


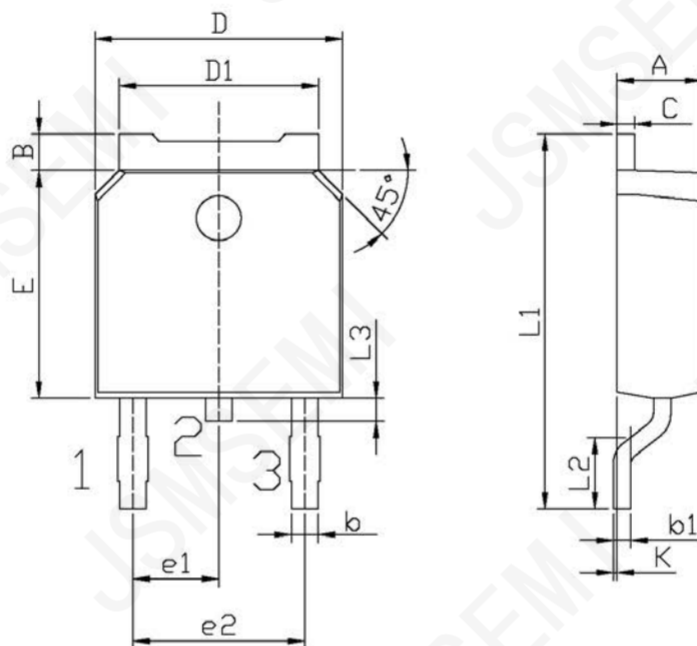
FIG. 4-TYPICAL REVERSE CHARACTERISTICS



Package Dimension

TO-252

Unit: mm



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.20	5.40	K	0.00	0.10